Darlington Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	55	Vdc
Collector - Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	12	Vdc
Collector Current – Continuous	I _C	1.0	Adc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

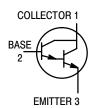
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta,IC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



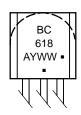
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



A = Assembly Location

′ = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC618	TO-92	5000 Units / Bulk
BC618G	TO-92 (Pb-Free)	5000 Units / Bulk
BC618RL1	TO-92	2000 / Tape & Reel
BC618RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u>.</u>			-	
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, V _{BE} = 0)	V _(BR) CEO	55	-	-	Vdc
Collector – Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	V _(BR) CBO	80	-	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	12	-	-	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{BE} = 0)	I _{CES}	_	_	50	nAdc
Collector Cutoff Current (V _{CB} = 60 Vdc, I _E = 0)	I _{CBO}	-	_	50	nAdc
Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)	I _{EBO}	_	_	50	nAdc
ON CHARACTERISTICS	<u>.</u>			-	
DC Current Gain ($I_C = 200 \text{ mA}, I_B = 0.2 \text{ mA}$)	V _{CE(sat)}	_	_	1.1	Vdc
Base – Emitter Saturation Voltage (I _C = 200 mA, I _B = 0.2 mA)	V _{BE(sat)}	_	_	1.6	Vdc
DC Current Gain $ \begin{array}{l} (I_C = 100 \; \mu A, \; V_{CE} = 5.0 \; \text{Vdc}) \\ (I_C = 10 \; \text{mA}, \; V_{CE} = 5.0 \; \text{Vdc}) \\ (I_C = 200 \; \text{mA}, \; V_{CE} = 5.0 \; \text{Vdc}) \\ (I_C = 1.0 \; \text{A}, \; V_{CE} = 5.0 \; \text{Vdc}) \end{array} $	h _{FE}	2000 4000 10000 4000	- - - -	- - 50000 -	-
DYNAMIC CHARACTERISTICS					
Current-Gain - Bandwidth Product (I _C = 500 mA, V _{CE} = 5.0 Vdc, P = 100 MHz)	f _⊤	150	-	-	MHz
Output Capacitance (V _{CB} = 10 V, I _E = 0, f = 1.0 MHz)	C _{ob}	-	4.5	7.0	pF
Input Capacitance (V _{EB} = 5.0 V, I _E = 0, f = 1.0 MHz)	C _{ib}	_	5.0	9.0	pF

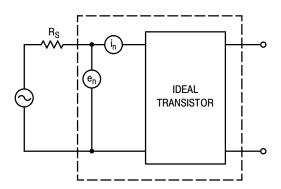


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

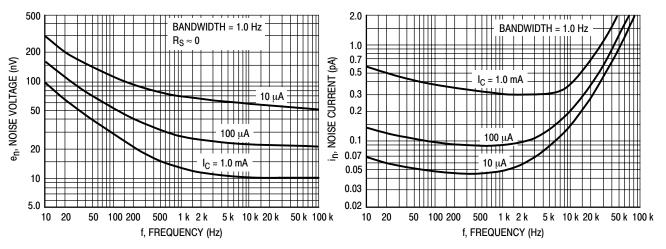


Figure 2. Noise Voltage

Figure 3. Noise Current

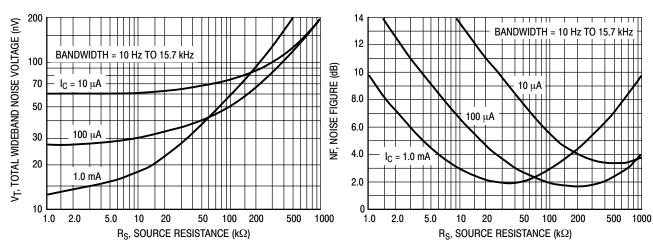
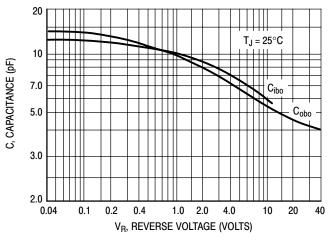


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

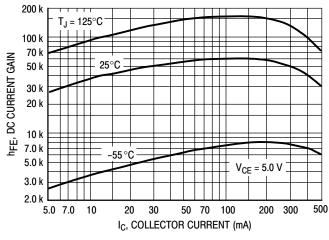
SMALL-SIGNAL CHARACTERISTICS



V_{CE} = 5.0 V |hfe|, SMALL-SIGNAL CURRENT GAIN f = 100 MHz $T_J = 25^{\circ}C$ 2.0 1.0 8.0 0.6 0.4 0.2 2.0 100 0.5 1.0 500 IC, COLLECTOR CURRENT (mA)

Figure 6. Capacitance

Figure 7. High Frequency Current Gain



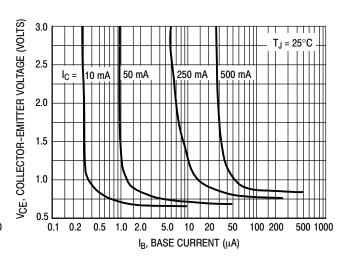
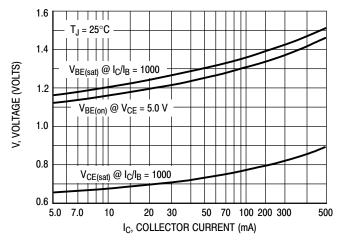


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region



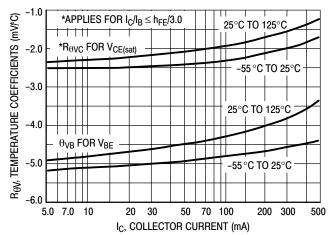


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

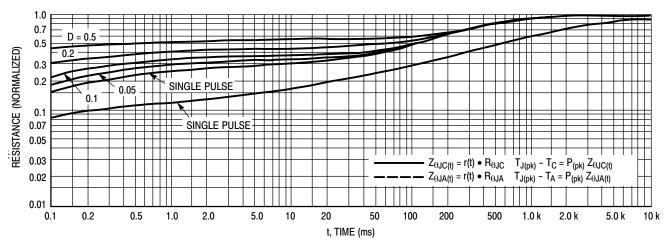


Figure 12. Thermal Response

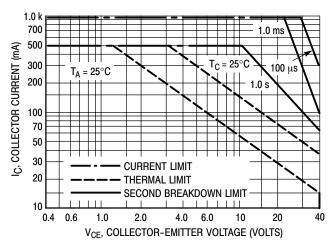
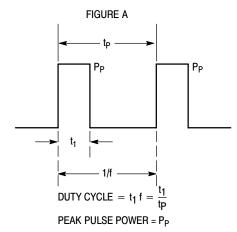


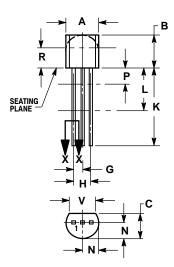
Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		INCHES MILLI		MILLIN	METERS	
DIM	MIN	MAX	MIN	MAX			
Α	0.175	0.205	4.45	5.20			
В	0.170	0.210	4.32	5.33			
С	0.125	0.165	3.18	4.19			
D	0.016	0.021	0.407	0.533			
G	0.045	0.055	1.15	1.39			
Н	0.095	0.105	2.42	2.66			
J	0.015	0.020	0.39	0.50			
K	0.500		12.70				
L	0.250		6.35				
N	0.080	0.105	2.04	2.66			
Р		0.100		2.54			
R	0.115		2.93				
٧	0.135		3.43				

STYLE 17:

PIN 1. COLLECTOR

- 2. BASE
- EMITTER

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